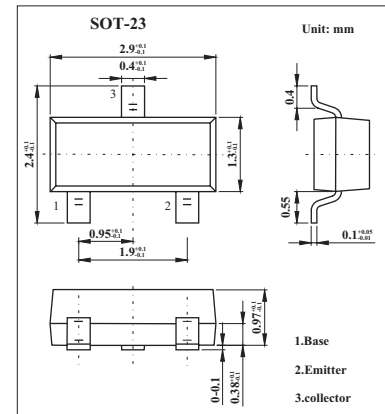


Silicon NPN Epitaxial

2SC2736

■ Features

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■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EBO}	3	V
Collector current	I _C	50	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10 μA, I _E = 0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1 mA, R _{BE} = ∞	20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10 μA, I _C = 0	3			V
Collector cutoff current	I _{CBO}	V _{CB} = 15 V, I _C = 0			500	nA
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 10 mA, I _B = 5 mA			0.7	V
DC current transfer ratio	h _{FE}	V _{CE} = 10 V, I _C = 5 mA	30		200	
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz			1.0	pF
Gain bandwidth product	f _T	V _{CE} = 10 V, I _C = 5 mA	1400	2200		MHz
Conversion gain	CG1	V _{CC} = 12 V, I _C = 2 mA, f = 200 MHz, f _{osc} = 230 MHz (0dBm)		22.5		dB
	CG2	V _{CC} = 12 V, I _C = 2 mA, f = 900 MHz, f _{osc} = 930 MHz (0dBm), f _{Out} = 30 MHz		10		dB
Noise figure	NF	V _{CC} = 12 V, I _C = 2 mA, f = 200 MHz, f _{osc} = 230 MHz (0dBm)		4.0		dB
Oscillating output voltage	V _{osc1}	V _{CC} = 12 V, I _C = 7 mA, f = 300 MHz		300		mV
	V _{osc2}	V _{CC} = 12 V, I _C = 7 mA, f _{osc} = 930 MHz		200		mV

■ Marking

Marking	TC